



America Semiconductor

Silicon Bridge Rectifier

GBPC35005TW thru GBPC3504TW

$V_{RRM} = 50\text{ V} - 1000\text{ V}$

$I_F = 35\text{ A}$

Features

- Integrally molded heat sink provides low thermal resistance for maximum heat dissipation
- Types up to 1000 V V_{RRM}
 - Void-free junction by using vacuum soldering
- High surge current capability
- High temperature soldering guaranteed: 260°C/ 10 seconds at 5 lbs(2.3 kg) tension
- Universal 3-way terminals: snap on, wire-around, or P.C board mounting

GBPC-T/W Package



Mechanical Data

Case: Molded plastic with heat sink mounted in the bridge

Mounting position: Bolt down on heat-sink with silicone thermal compound between bridge and mounting surface

Terminals: Either nickel plated 0.25"(6.35 mm) Faston lugs or 0.040"(1.02 mm) diameter copper leads.

Weight: 15 grams or 0.53 ounces

Mounting torque: 20 inch-lbs max

Polarity: Marked on body

Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified (GBPCXXXXT uses GBPC-T package while GBPCXXXXW uses GBPC-W package)

| Parameter | Symbol | Conditions | GBPC35005T/W | GBPC3501T/W | GBPC3502T/W | GBPC3504T/W | Unit |
|--|------------|--|--------------|-------------|-------------|-------------|------------------|
| Repetitive peak reverse voltage | V_{RRM} | | 50 | 100 | 200 | 400 | V |
| RMS reverse voltage | V_{RMS} | | 35 | 70 | 140 | 280 | V |
| DC blocking voltage | V_{DC} | | 50 | 100 | 200 | 400 | V |
| Continuous forward current | I_F | $T_C \leq 50\text{ }^\circ\text{C}$ | 35 | 35 | 35 | 35 | A |
| Surge non-repetitive forward current, Half Sine Wave | $I_{F,SM}$ | $T_C = 25\text{ }^\circ\text{C}$, $t_p = 8.3\text{ ms}$ | 400 | 400 | 400 | 400 | A |
| Operating temperature | T_j | | -55 to 150 | -55 to 150 | -55 to 150 | -55 to 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | | -55 to 150 | -55 to 150 | -55 to 150 | -55 to 150 | $^\circ\text{C}$ |

Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | GBPC35005T/W | GBPC3501T/W | GBPC3502T/W | GBPC3504T/W | Unit |
|-----------------------|--------|---|--------------|-------------|-------------|-------------|---------------|
| Diode forward voltage | V_F | $I_F = 17.5\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$ | 1.1 | 1.1 | 1.1 | 1.1 | V |
| Reverse current | I_R | $V_R = 50\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$ $V_R = 50\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$ | 5 500 | 5 500 | 5 500 | 5 500 | μA |

Thermal characteristics

| | | | | | | | |
|-------------------------------------|------------|--|-----|-----|-----|-----|--------------------|
| Thermal resistance, junction - case | R_{thJC} | | 1.4 | 1.4 | 1.4 | 1.4 | $^\circ\text{C/W}$ |
|-------------------------------------|------------|--|-----|-----|-----|-----|--------------------|





America Semiconductor

GBPC35005TW thru GBPC3504TW

FIG.5-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS PER LEG

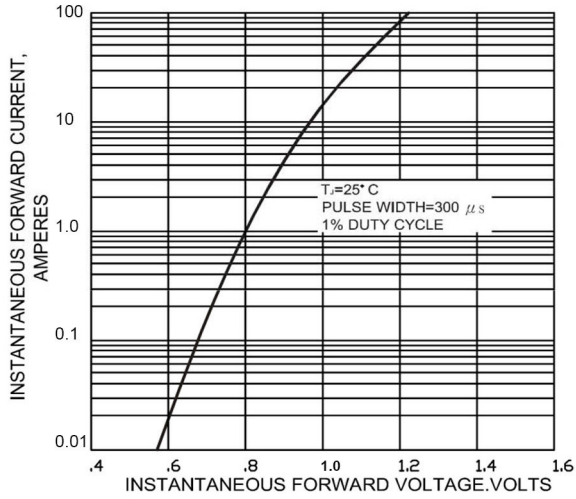


FIG.6-TYPICAL REVERSE CHARACTERISTICS

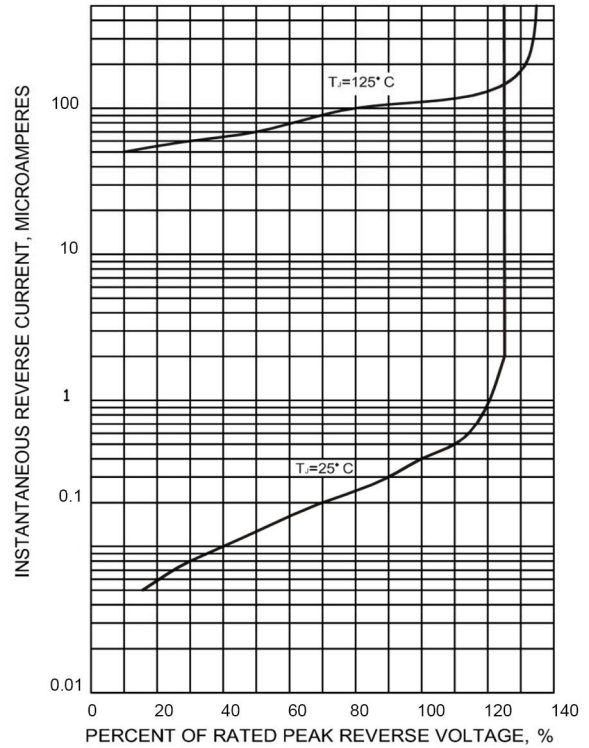


FIG.7-TYPICAL JUNCTION CAPACITANCE PER LEG

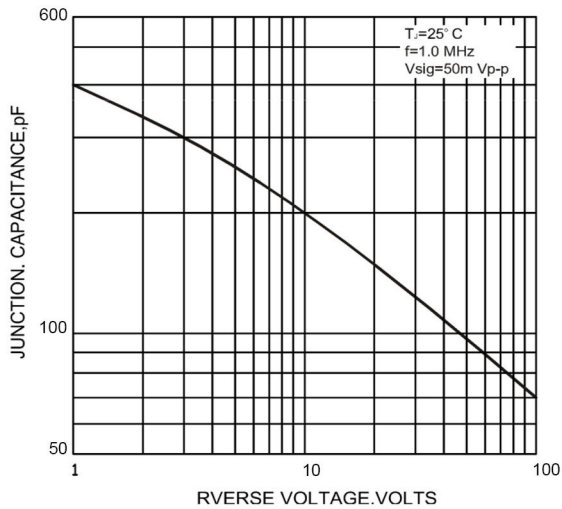


FIG.8-TYPICAL TRANSIENT THERMAL IMPEDANCE

